



Product Summary

BV _{DSS}	Rds(on) max	I _{D MAX} T _A = +25°C
20V	$28m\Omega @ V_{GS} = 4.5V$	5.8A
	$32m\Omega @ V_{GS} = 2.5V$	5.4A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- **DC-DC** Converters
- **Power Management Functions**

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

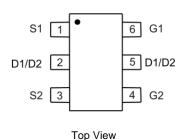
- Low On-Resistance .
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.
- https://www.diodes.com/guality/product-definitions/

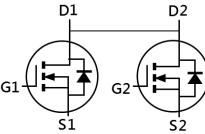
Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.013 grams (Approximate)



TSOT26





Equivalent Circuit

Ordering Information (Note 4)

	Part Number	Case	Packaging			
	DMN2041UVT-7	TSOT26	3000 / Tape & Reel			
	DMN2041UVT-13	10000 / Tape & Reel				
Notes:	2012/2012/2012/2012/2012/2012/2012/2012					

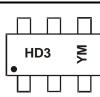
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



HD3 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Kev

Year	2019		2020	2021		2022	2023		2024	2025		2026
Code	G		Н	I		J	K		L	М		Ν
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit		
Drain-Source Voltage		V _{DSS}	20	V		
Gate-Source Voltage	V _{GSS}	±8	V			
	Steady	T _A = +25°C		5.8	A	
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$	State	T _A = +70°C	ID	4.6		
Maximum Continuous Body Diode Forward Curre	ent (Note 6)	ls	1.3	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%)	I _{DM}	36	А		

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	1.1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	113	°C/W
Total Power Dissipation (Note 6)		PD	0.92	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	87	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					•	
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	_	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	I _{DSS}	—	—	1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	IGSS	_	-	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)			-			
Gate Threshold Voltage	V _{GS(TH)}	0.4	—	0.9	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
			17	28		$V_{GS} = 4.5V, I_D = 8.2A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	22	32	mΩ	$V_{GS} = 2.5V, I_D = 3.3A$
			32	40		$V_{GS} = 1.8V, I_D = 2.0A$
Diode Forward Voltage	V _{SD}	_	0.7	0.9	V	$V_{GS} = 0V, I_D = 2.25A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	—	689	-	pF	
Output Capacitance		_	89	—	pF	$V_{DS} = 10V, V_{GS} = 0V$ - f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	79	_	pF	
Gate Resistance	Rg	—	1.05	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Qg	—	9.1	_	nC	
Gate-Source Charge	Qgs	—	0.3	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 8.2A$
Gate-Drain Charge	Q _{gd}	—	2.1	_	nC	
Turn-On Delay Time	t _{D(ON)}	_	9	—	ns	
Turn-On Rise Time	t _R	—	21	—	ns	$V_{DS} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	—	32	—	ns	$R_L = 10\Omega, R_g = 6\Omega, I_D = 1A$
Turn-Off Fall Time	t _F	—	17	_	ns	

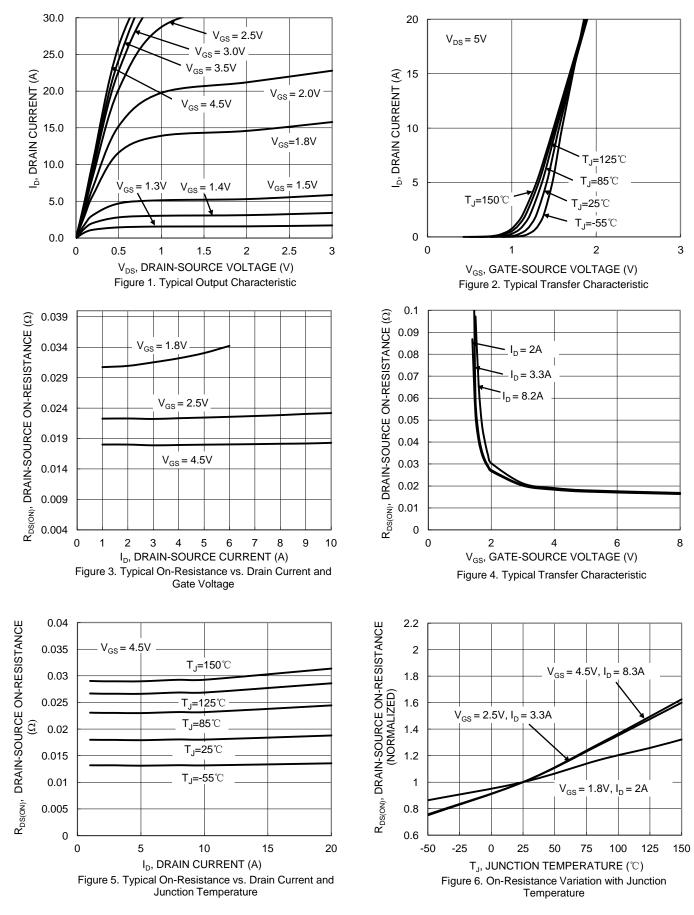
Notes:

Device mounted on FR-4 PCB, with minimum recommended pad layout.
Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.



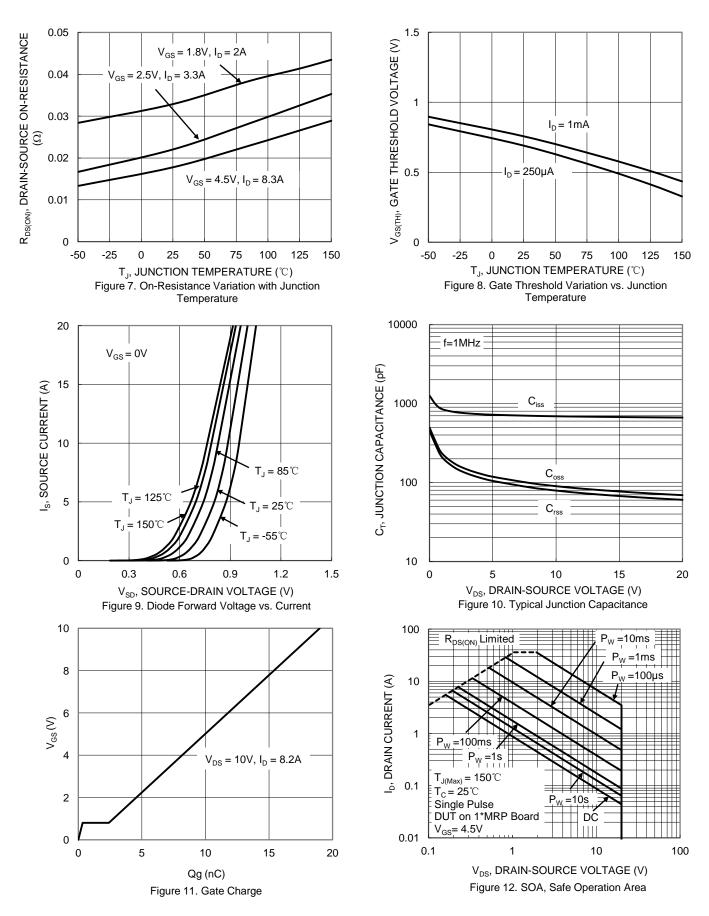
DMN2041UVT



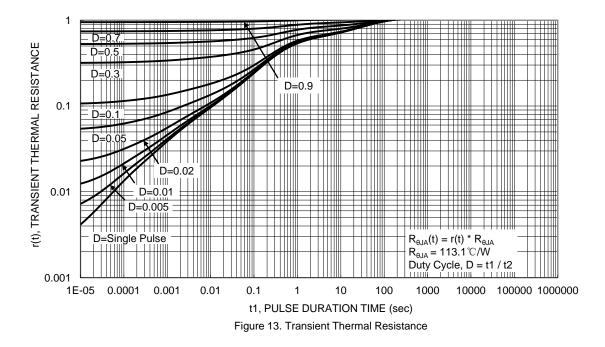
DMN2041UVT Document number: DS41720 Rev. 2 - 2 October 2019 © Diodes Incorporated



DMN2041UVT



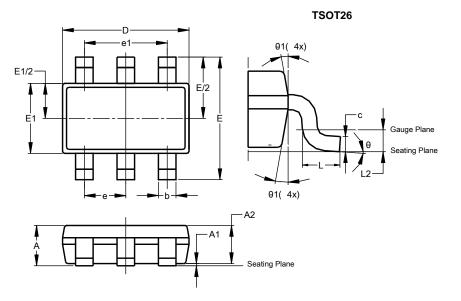






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

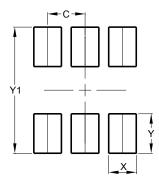


	TSOT26							
Dim	Min	Max	Тур					
Α	-	1.00	-					
A1	0.010	0.100	-					
A2	0.840	0.900	-					
D	2.800	3.000	2.900					
Е	2	.800 BS	С					
E1	1.500	1.700	1.600					
b	0.300	0.450	-					
С	0.120	0.200	-					
е	0	0.950 BSC						
e1	1	.900 BS	С					
L	0.30	0.50	-					
L2	0.250 BSC							
θ	0°	8°	4°					
θ1	4°	12°	-					
A	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199



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